Nathan Newman

List of Publications by Year
in descending order

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142	5,004	87723	102304
papers	citations	38 h-index	66 g-index

152	152	152	3551
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Biâ€epitaxial grain boundary junctions in YBa2Cu3O7. Applied Physics Letters, 1991, 59, 733-735.	1.5	299
2	Role of Embedded Clustering in Dilute Magnetic Semiconductors: Cr Doped GaN. Physical Review Letters, 2005, 95, 256404.	2.9	212
3	Observation of ferromagnetism above 900K in Crâ€“GaN and Crâ€“AlN. Applied Physics Letters, 2004, 85, 4076-4078.	1.5	207
4	1.54â€Î¼m photoluminescence from Erâ€implanted GaN and AlN. Applied Physics Letters, 1994, 65, 992-994.	1.5	197
5	Scanning tunneling microscopy studies of Si donors (SiGa) in GaAs. Physical Review Letters, 1994, 72, 1490-1493.	2.9	193
6	High-temperature superconducting microwave devices: Fundamental issues in materials, physics, and engineering. Journal of Superconductivity and Novel Magnetism, 1993, 6, 119-160.	0.5	167
7	pâ€type gallium nitride by reactive ionâ€beam molecular beam epitaxy with ion implantation, diffusion, or coevaporation of Mg. Applied Physics Letters, 1994, 64, 64-66.	1.5	167
8	Synthesis, characterization, and modeling of high quality ferromagnetic Cr-doped AlN thin films. Applied Physics Letters, 2003, 82, 3047-3049.	1.5	166
9	Electrical study of Schottky barriers on atomically clean GaAs(110) surfaces. Physical Review B, 1986, 33, 1146-1159.	1.1	140
10	Spin lifetimes of electrons injected into GaAs and GaN. Applied Physics Letters, 2003, 83, 1761-1763.	1.5	109
11	Microwave surface resistance of epitaxial YBa2Cu3O7thin films on sapphire. Applied Physics Letters, 1990, 57, 409-411.	1.5	108
12	Largeâ€area YBa2Cu3O7â^Îthin films on sapphire for microwave applications. Applied Physics Letters, 1992, 61, 1727-1729.	1.5	104
13	YBa2Cu3O7â^Îsuperconducting films with low microwave surface resistance over large areas. Applied Physics Letters, 1990, 57, 520-522.	1.5	99
14	Observation of two inâ€plane epitaxial states in YBa2Cu3O7â^Îfilms on yttriaâ€stabilized ZrO2. Applied Physics Letters, 1991, 58, 2168-2170.	1.5	97
15	Low-Temperature Structural Transitions in the Phonon-Glass Thermoelectric Material Î²-Zn4Sb3:Â Ordering of Zn Interstitials and Defects. Chemistry of Materials, 2007, 19, 834-838.	3.2	89
16	Electrical study of Schottky barrier heights on atomically clean and airâ€exposednâ€InP(110) surfaces. Applied Physics Letters, 1985, 46, 1176-1178.	1.5	82
17	Thermodynamic and kinetic processes involved in the growth of epitaxial GaN thin films. Applied Physics Letters, 1993, 62, 1242-1244.	1.5	82
18	Experimental study of MgB2 decomposition. Applied Physics Letters, 2001, 79, 87-89.	1.5	82

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19	Suppression of the Critical Temperature of Superconducting NdFeAs(OF) Single Crystals by Kondo-Like Defect Sites Induced by<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>Î±</mml:mi></mml:math>-Particle Irradiation. Physical Review Letters, 2010, 104, 087002.	2.9	70
20	Electron microscopy characterization of GaN films grown by molecular-beam epitaxy on sapphire and SiC. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 1578.	1.6	69
21	The energetics of the GaN MBE reaction: a case study of meta-stable growth. Journal of Crystal Growth, 1997, 178, 102-112.	0.7	65
22	The mechanisms of Schottky barrier pinning in IIIâ€“V semiconductors: Criteria developed from microscopic (atomic level) and macroscopic experiments. Surface Science, 1986, 168, 240-259.	0.8	63
23	Internally shunted sputtered NbN Josephson junctions with a TaNx barrier for nonlatching logic applications. Applied Physics Letters, 2001, 78, 99-101.	1.5	62
24	Engineered Schottky barrier diodes for the modification and control of Schottky barrier heights. Journal of Applied Physics, 1987, 61, 5159-5169.	1.1	59
25	Double gun off-axis sputtering of large area YBa/sub 2/Cu/sub 3/O/sub 7- delta / superconducting films for microwave applications. IEEE Transactions on Magnetics, 1991, 27, 1276-1279.	1.2	57
26	High critical current densities in epitaxial YBa2Cu3O7âˆ’Î´thin films on siliconâ€onâ€sapphire. Applied Physics Letters, 1991, 58, 2432-2434.	1.5	57
27	Thermochemistry of MgB/sub 2/ thin film synthesis. IEEE Transactions on Applied Superconductivity, 2003, 13, 3238-3241.	1.1	57
28	Effect of metal doping on the low-temperature structural behavior of thermoelectric Î²-Zn4Sb3. Journal of Solid State Chemistry, 2007, 180, 2603-2615.	1.4	57
29	Electronic structure of ideal metal/GaAs contacts. Physical Review Letters, 1990, 65, 2728-2731.	2.9	52
30	Switching at small magnetic fields in Josephson junctions fabricated with ferromagnetic barrier layers. Applied Physics Letters, 2014, 104, .	1.5	49
31	Electrical study of Schottky-barrier heights on atomically cleanp-type InP(110) surfaces. Physical Review B, 1987, 35, 6298-6304.	1.1	47
32	Thermal annealing characteristics of Si and Mgâ€implanted GaN thin films. Applied Physics Letters, 1996, 68, 2702-2704.	1.5	43
33	Fabrication and measurement of high T/sub c/ superconducting microbolometers. IEEE Transactions on Magnetics, 1991, 27, 3081-3084.	1.2	41
34	Half-Metallicity and Efficient Spin Injection inAlN/GaNâˆ¶Cr(0001) Heterostructure. Physical Review Letters, 2005, 94, 146602.	2.9	41
35	Comparative Study of the Thermoelectric Properties of Amorphous Zn₄₁Sb₅₉ and Crystalline Zn₄Sb₃. Chemistry of Materials, 2009, 21, 151-155.	3.2	41
36	Electronic structure and Schottky-barrier formation of Ag onn-type GaAs(110). Physical Review B, 1985, 32, 918-923.	1.1	39

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37	One-pot synthesis of highly mesoporous antimony-doped tin oxide from interpenetrating inorganic/organic networks. Journal of Materials Chemistry, 2011, 21, 13232.	6.7	39
38	Defect energy levels and electronic behavior of Ni-, Co-, and As-doped synthetic pyrite (FeS2). Journal of Applied Physics, 2012, 111, .	1.1	38
39	Experimental determination of the rates of decomposition and cation desorption from AlN surfaces. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 87, 244-248.	1.7	36
40	Homoepitaxial growth of GaN using molecular beam epitaxy. Journal of Applied Physics, 1996, 80, 2195-2198.	1.1	35
41	Role of Ni and Zr doping on the electrical, optical, magnetic, and structural properties of barium zinc tantalate ceramics. Journal of Materials Research, 1999, 14, 4011-4019.	1.2	35
42	Defect annihilation in AlN thin films by ultrahigh temperature processing. Applied Physics Letters, 2000, 76, 1839-1841.	1.5	35
43	Observation of stimulated emission in the near ultraviolet from a molecular beam epitaxy grown GaN film on sapphire in a verticalâ€cavity, single pass configuration. Applied Physics Letters, 1994, 64, 1135-1137.	1.5	34
44	Hollowâ€anode plasma source for molecular beam epitaxy of gallium nitride. Review of Scientific Instruments, 1996, 67, 905-907.	0.6	34
45	The influence of nitrogen ion energy on the quality of GaN films grown with molecular beam epitaxy. Journal of Electronic Materials, 1995, 24, 249-255.	1.0	33
46	Annealing of intimate Auâ€GaAs Schottky barriers: Thick and ultrathin metal films. Journal of Applied Physics, 1985, 57, 1247-1251.	1.1	30
47	Morphology of Au/GaAs interfaces. Applied Physics Letters, 1986, 49, 1514-1516.	1.5	29
48	Microwave Loss in the High-Performance Dielectric<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>Ba</mml:mi><mml:mo stretchy="false">(</mml:mo><mml:msub><mml:mi>Zn</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>/</mml:mo><mml:mn mathvariant="bold">O</mml:mi><mml:mn>3</mml:mn></mml. Physical Review Letters, 2012, 109, 257601.	2.9	29
49	Residual losses in epitaxial thin films of YBa2Cu3O7from microwave to submillimeter wave frequencies. Applied Physics Letters, 1991, 59, 2326-2328.	1.5	28
50	High-temperature superconductive devices on sapphire. IEEE Transactions on Microwave Theory and Techniques, 1994, 42, 34-40.	2.9	27
51	Growth and characterization of epitaxial Ba(Zn1/3Ta2/3)O3 (100) thin films. Acta Materialia, 2009, 57, 432-440.	3.8	26
52	High temperature growth of AlN by plasma-enhanced molecular beam epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 67, 80-87.	1.7	25
53	High-temperature superconductor resonators and phase shifters. IEEE Transactions on Applied Superconductivity, 1991, 1, 58-66.	1.1	24
54	Metastable Cd4Sb3: A Complex Structured Intermetallic Compound with Semiconductor Properties. Journal of the American Chemical Society, 2008, 130, 15564-15572.	6.6	24

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55	Correspondence between microwave and submillimeter absorptivity in epitaxial thin films ofYBa2Cu3O7. Physical Review B, 1993, 47, 8076-8088.	1.1	23
56	Precise control of atomic nitrogen production in an electron cyclotron resonance plasma using N2/noble gas mixtures. Applied Physics Letters, 1998, 73, 456-458.	1.5	23
57	Fabrication of Niobium Titanium Nitride Thin Films With High Superconducting Transition Temperatures and Short Penetration Lengths. IEEE Transactions on Applied Superconductivity, 2005, 15, 44-48.	1.1	23
58	Structureâ€“dielectric property relationship for vanadium- and scandium-doped barium strontium titanate. Acta Materialia, 2007, 55, 2647-2657.	3.8	22
59	Internally shunted Josephson junctions with barriers tuned near the metalâ€“insulator transition for RSFQ logic applications. Superconductor Science and Technology, 2006, 19, 719-731.	1.8	21
60	Schottky barrier instabilities due to contamination. Applied Physics Letters, 1988, 53, 145-147.	1.5	20
61	First direct observation of EL2-like defect levels in annealed LT-GaAS. Journal of Electronic Materials, 1993, 22, 1499-1502.	1.0	20
62	Nanoporous Delafossite CuAlO₂ from Inorganic/Polymer Double Gels: A Desirable High-Surface-Area p-Type Transparent Electrode Material. Inorganic Chemistry, 2015, 54, 1100-1108.	1.9	20
63	Pressure Dependence of III-V Schottky Barriers: A Critical Test of Theories for Fermi Level Pinning. Physical Review Letters, 1994, 73, 581-584.	2.9	19
64	Thin film tandem photovoltaic cell from II-IV-V chalcopyrites. Applied Physics Letters, 2010, 96, 143503.	1.5	18
65	The dominance of paramagnetic loss in microwave dielectric ceramics at cryogenic temperatures. Applied Physics Letters, 2012, 101, .	1.5	18
66	Stacking faults in quaternary In Al Ga1â^'â^'N layers. Acta Materialia, 2008, 56, 4036-4045.	3.8	17
67	Main Source of Microwave Loss in Transitionâ€Metalâ€Doped Ba(Zn_{1/3}Ta_{2/3})O₃ and Ba(Zn_{1/3}Nb_{2/3})O₃ at Cryogenic Temperatures. Journal of the American Ceramic Society, 2015, 98, 1188-1194.	1.9	17
68	Aluminum Schottky barrier formation on arsenic capped and heat cleaned MBE GaAs(100). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1984, 2, 481.	1.6	16
69	Schottky barriers on atomically clean cleaved GaAs. Solid-State Electronics, 1985, 28, 307-312.	0.8	16
70	Bandpass filters using dual-mode and quad-mode Mobius resonators. IEEE Transactions on Microwave Theory and Techniques, 2001, 49, 2363-2368.	2.9	16
71	Fundamental mechanisms responsible for the temperature coefficient of resonant frequency in microwave dielectric ceramics. Journal of the American Ceramic Society, 2017, 100, 1508-1516.	1.9	16
72	Experimental determination of the pressure dependence of the barrier height of metal/[n-type GaAs] Schottky contacts: A critical test of Schottky-barrier models. Physical Review B, 1995, 51, 18003-18006.	1.1	15

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73	Control of the structure and surface morphology of gallium nitride and aluminum nitride thin films by nitrogen background pressure in pulsed laser deposition. Journal of Electronic Materials, 1998, 27, 215-221.	1.0	15
74	Thermochemical analysis of MgB2 synthesis by molecular-beam epitaxy. Journal of Crystal Growth, 2004, 270, 107-112.	0.7	15
75	Large magnetoresistance of thick polymer devices having La0.67Sr0.33MnO3 electrodes. Applied Physics Letters, 2009, 95, .	1.5	15
76	Effects of stress on phase separation in InxGa1â^'xN/GaN multiple quantum-wells. Acta Materialia, 2011, 59, 3759-3769.	3.8	15
77	Origin of dielectric loss in Ba(Co_{1/3}Nb_{2/3})O₃ microwave ceramics. Journal of the American Ceramic Society, 2018, 101, 1665-1676.	1.9	15
78	Ordered domains and boundary structure in Ba(Cd1/3Ta2/3)O3 perovskite dielectrics. Applied Physics Letters, 2004, 84, 3918-3920.	1.5	14
79	Electrical conductivities and Li ion concentration-dependent diffusivities, in polyurethane polymers doped with lithium trifluoromethanesulfonimide (LiTFSI) or lithium perchlorate (LiClO4). Solid State Ionics, 2010, 181, 1727-1731.	1.3	14
80	Aging of Schottky diodes formed on airâ€exposed and atomically clean GaAs surfaces: An electrical study. Journal of Applied Physics, 1988, 63, 2006-2010.	1.1	13
81	Electrical transport properties of ferromagnetic GaxCr1â^'xN thin films. Applied Physics Letters, 2006, 89, 142105.	1.5	13
82	Nanoscale disorder in pure and doped MgB₂thin films. Superconductor Science and Technology, 2010, 23, 095008.	1.8	13
83	Criteria for improving the properties of ZnGeAs₂ solar cells. Progress in Photovoltaics: Research and Applications, 2013, 21, 906-917.	4.4	13
84	Measurement of the coherence length of sputtered Nb/sub 0.62/Ti/sub 0.38/N thin films. IEEE Transactions on Applied Superconductivity, 2002, 12, 1795-1798.	1.1	12
85	Microstructure and dielectric properties of Ba(Cd1/3Ta2/3)O3 microwave ceramics synthesized with a boron oxide sintering aid. Journal of Materials Research, 2004, 19, 3526-3533.	1.2	12
86	Phase separation and atomic ordering in InxAlyGa1â^'xâ^'yN layers. Acta Materialia, 2008, 56, 5552-5559.	3.8	12
87	[0001] composition modulations in Al0.4Ga0.6N layers grown by molecular beam epitaxy. Applied Physics Letters, 2008, 92, 261914.	1.5	12
88	Fabrication of highly spin-polarized Co2FeAl0.5Si0.5 thin-films. APL Materials, 2014, 2, .	2.2	12
89	Influence of the exchange reaction on the electronic structure of GaN/Al junctions. Physical Review B, 1998, 58, 7906-7912.	1.1	11
90	Effect of oxygen incorporation on normal and superconducting properties of MgB2 films. Applied Physics Letters, 2008, 93, 242504.	1.5	11

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91	Leakage-current characteristics of vanadium- and scandium-doped barium strontium titanate ceramics over a wide range of DC electric fields. Acta Materialia, 2009, 57, 4935-4947.	3.8	11
92	The magnetic, electrical and structural properties of copper-permalloy alloys. Journal of Magnetism and Magnetic Materials, 2017, 442, 45-52.	1.0	11
93	Electronic properties of metal/IIIâ€“V semiconductor interfaces. Surface Science, 1985, 162, 591-604.	0.8	10
94	Atomic Resolution Transmission Electron Microscopy of the Microstructure of Ordered Ba(Cd1/3Ta2/3)O3 Perovskite Ceramics. Journal of the American Ceramic Society, 2006, 89, 1047-1052.	1.9	10
95	Effect of non-stoichiometry on the densification, phase purity, microstructure, crystal structure, and dielectric loss of Ba(Co 1/3 Nb 2/3)O 3 ceramics. Journal of the European Ceramic Society, 2017, 37, 3335-3346.	2.8	9
96	Influence of interfacial contamination on the structure and barrier height of Cr/GaAs Schottky contacts. Applied Physics Letters, 1989, 54, 356-358.	1.5	8
97	Growth of epitaxial pyrite (FeS2) thin films using sequential evaporation. Acta Materialia, 2013, 61, 7392-7398.	3.8	8
98	Zn5Sb4In2â˜Î´ â€” a Ternary Derivative of Thermoelectric Zinc Antimonides. Inorganic Chemistry, 2009, 48, 5996-6003.	1.9	7
99	Characterization of Josephson and quasi-particle currents in MgB2/MgB2and Pb/Pb contact junctions. Superconductor Science and Technology, 2010, 23, 075003.	1.8	7
100	Influence of surface topography on in situ reflection electron energy loss spectroscopy plasmon spectra of AlN, GaN, and InN semiconductors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2011, 29, .	0.9	7
101	Effect ofÎ±-particle irradiation on a NdFeAs(O,F) thin film. Superconductor Science and Technology, 2018, 31, 034002.	1.8	7
102	Magnetic properties of chromium-doped Ni80Fe20 thin films. Journal of Magnetism and Magnetic Materials, 2018, 460, 193-202.	1.0	7
103	Mechanism for nearly ohmic behavior in annealed Au/nâ€GaAs Schottky diodes. Journal of Applied Physics, 1989, 66, 711-715.	1.1	6
104	Submillimeter and microwave residual losses in epitaxial films of Y-Ba-Cu-O and Tl-Ca-Ba-Cu-O. Journal of Superconductivity and Novel Magnetism, 1992, 5, 379-388.	0.5	6
105	Electron microscopy characterization of Ba(Cd1/3Ta2/3)O3 microwave dielectrics with boron additive. Journal of Materials Research, 2004, 19, 1387-1391.	1.2	6
106	Structural, chemical and dielectric properties of ceramic injection moulded Ba(Zn1/3Ta2/3)O3 microwave dielectric ceramics. Journal of the European Ceramic Society, 2006, 26, 3273-3278.	2.8	6
107	Growth and characterization of Ba(Cd1/3Ta2/3)O3 thin films. Thin Solid Films, 2012, 520, 6153-6157.	0.8	6
108	Structural, electrical, and thermoelectric properties of CrSi 2 thin films. Thin Solid Films, 2013, 545, 100-105.	0.8	6

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109	van Schilfgaarde and Newman reply. Physical Review Letters, 1991, 67, 282-282.	2.9	5
110	Incorporation of a Frequency-Dependent Dielectric Response for the Barrier Material in the Josephson Junction Circuit Model. IEEE Transactions on Applied Superconductivity, 2005, 15, 3886-3900.	1.1	5
111	Metalâ€“nonmetal transition in the sphalerite-type solid solution [ZnSnSb2]1â^'x[2(InSb)]x. Journal of Solid State Chemistry, 2009, 182, 1438-1442.	1.4	5
112	Thermoelectric properties of Zn5Sb4In2-Î´ (Îˆâ€‰=â€‰0.15). Journal of Applied Physics, 2012, 111, 123712.	1.1	5
113	Investigations of the disorder in the TaxN thin films: On the first order Raman spectrum of the rock salt crystal structure. Journal of Applied Physics, 2013, 114, .	1.1	5
114	Influence of substrate temperature on properties of pyrite thin films deposited using a sequential coevaporation technique. Thin Solid Films, 2019, 669, 49-55.	0.8	5
115	Low-temperature synthesis of 2D anisotropic MoTe2 using a high-pressure soft sputtering technique. Nanoscale Advances, 2020, 2, 1443-1448.	2.2	5
116	High temperature superconducting transresistance amplifiers for far infrared detectors. IEEE Transactions on Applied Superconductivity, 1992, 2, 111-113.	1.1	4
117	Cd13â^'xInySb10(xâ‰ˆ2.7,yâ‰ˆ1.5): An Interstitial-Free Variant of Thermoelectric Î²-Zn4Sb3. Chemistry - A European Journal, 2009, 15, 6704-6710.	1.7	4
118	Electrical properties of AsxSe1â^'x (xâ‰¥0.05) Mott-barriers. Journal of Non-Crystalline Solids, 2011, 357, 3366-3372.	1.5	4
119	Clean to dirty limit andT_csuppression in NdFeAsO_{0.7}F_{0.3}studied byH_{c2}analysis. Superconductor Science and Technology, 2018, 31, 034007.	1.8	4
120	Better Resolution of High-Spin Cobalt Hyperfine at Low Frequency: Co-Doped Ba(Zn1/3Ta2/3)O3 as a Model Complex. International Journal of Molecular Sciences, 2018, 19, 3532.	1.8	4
121	Switching microwave dielectric resonators from a high-Q on state to an off state using low-field electron paramagnetic resonance transitions. Applied Physics Letters, 2018, 113, .	1.5	4
122	van Schilfgaarde and Newman reply. Physical Review Letters, 1991, 67, 2746-2746.	2.9	3
123	Structural, Dielectric, and Optical Properties of Ni-Doped Barium Cadmium Tantalate Ceramics. Japanese Journal of Applied Physics, 2006, 45, 9140-9142.	0.8	3
124	Low-temperature transport properties of Ta_xN thin films (0.72 â©½ x â©½ 0.83). Journal Physics D: Applied Physics, 2010, 43, 445405.	1.3	3
125	High Energy and Spatial Resolution EELS Band Gap Measurements Using a Nion Monochromated Cold Field Emission HERMES Dedicated STEM. Microscopy and Microanalysis, 2014, 20, 70-71.	0.2	2
126	Growth and characterization of epitaxial Ba(Co,Zn)1/3Nb2/3O3 thin films. Journal of Crystal Growth, 2014, 387, 81-85.	0.7	2

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127	In-situ electron paramagnetic resonance studies of paramagnetic point defects in superconducting microwave resonators. Applied Physics Letters, 2016, 109, .	1.5	2
128	Low microwave loss in deposited Si and Ge thin-film dielectrics at single-photon power and low temperatures. AIP Advances, 2021, 11, .	0.6	2
129	Magnetically tuning the loss tangent in La(Al1â^'xFex)O3 using low field electron paramagnetic resonance transitions. Applied Physics Letters, 2020, 117, 222901.	1.5	2
130	Effect of heat treatment on the properties of non-stoichiometric Ba3CoNb2O9 ceramics: Evaluation of crystal structure, order-disorder behavior, and dielectric characteristics. Journal of the European Ceramic Society, 2022, 42, 3224-3224.	2.8	2
131	Theoretical and Experimental Study of Barium Zinc-Cadmium Tantalate-based Microwave Dielectrics. Materials Research Society Symposia Proceedings, 2003, 783, 471.	0.1	1
132	Saturation and intrinsic dynamics of fluxons in NbTi and MgB2. Applied Physics Letters, 2007, 90, 132504.	1.5	1
133	The Southwestern Center for Aberration Corrected Electron Microscopy at Arizona State University: The Facility. Microscopy and Microanalysis, 2012, 18, 408-409.	0.2	1
134	Experimental study of the kinetically-limited decomposition of ZnGeAs2 and its role in determining optimal conditions for thin film growth. Journal of Crystal Growth, 2012, 338, 267-271.	0.7	1
135	Effect of Helium Ion Irradiation on the Tunneling Behavior in Niobium/Aluminumâ€“Aluminum Oxide/Niobium Josephson Junctions. IEEE Transactions on Applied Superconductivity, 2013, 23, 1101610-1101610.	1.1	1
136	Kinetic Processes in Vapor PhaseÂEpitaxy. , 2015, , 835-868.		1
137	Improvement in the Magnetic Properties of Niâ€“Fe Thin Films on Thick Nb Electrodes Using Oxidation and Low-Energy Ar Ion Milling. IEEE Magnetics Letters, 2018, 9, 1-4.	0.6	1
138	Large Uniaxial Anisotropy Induced in Soft Ferromagnetic Thin Films by Oblique Deposition of Underlayer. IEEE Magnetics Letters, 2018, 9, 1-5.	0.6	1
139	First principles study of phase stability in Ba-based tantalate complex double perovskites. Applied Physics Letters, 2021, 119, 052901.	1.5	1
140	Electromagnetic bandgap resonators synthesized using ceramic injection molding. Microwave and Optical Technology Letters, 2014, 56, 371-375.	0.9	0
141	Development of magnetically switchable high permittivity microwave dielectrics using La(Al_{1â€x}Fe_x)O₃. Journal of the American Ceramic Society, 2021, 104, 2669-2677.	1.9	0
142	Working with Frank Wilczek to Make the Invisible, Visible. , 2022, , 181-184.		0